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Vishay Siliconix

N-Channel 250-V (D-S) 175 °C MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	V _{DS} (V) R _{DS(on)} (Ω)				
250	0.165 at V _{GS} = 10 V	17			

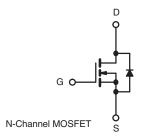


FEATURES

- TrenchFET® power MOSFET
- 175 °C junction temperature







Ordering Information:

SUD17N25-165-E3 (lead (Pb)-free)

ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C, unless otherwise noted)						
PARAMETER	SYMBOL	LIMIT	UNIT			
Drain-Source Voltage	V_{DS}	250				
Gate-Source Voltage	V_{GS}	± 20	V			
Continuous Drain Current (T,I = 175 °C) b	T _C = 25 °C	1	17			
Continuous Drain Current (1) = 175 C) ~	T _C = 125 °C	l _D	9.8			
Pulsed Drain Current	I _{DM}	20	А			
Continuous Source Current (Diode Conduction)	Is	17				
Single Pulse Avalanche Current	I _{AS}	4				
Single Pulse Avalanche Energy	Avalanche Energy $L = 0.3 \text{ mH}$ E_{AS}		2.4	mJ		
Maximum Power Dissipation	T _C = 25 °C	В	136 ^b	W		
iviaximum rowei bissipation	T _A = 25 °C	P_D	3 ^a			
Operating Junction and Storage Temperature Range	T _J , T _{stg}	-55 to +175	°C			

THERMAL RESISTANCE RATINGS							
PARAMETER		SYMBOL	TYPICAL	MAXIMUM	UNIT		
Junction-to-Ambient ^a	t ≤ 10 s	- R _{thJA}	15	18	°C/W		
Junction-to-Ambient 4	Steady State		40	50			
Junction-to-Case (Drain)		R _{thJC}	0.85	1.1			

Notes

- a. Surface mounted on 1" x 1" FR4 board.
- b. See SOA curve for voltage derating.



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PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP. a	MAX.	UNIT	
Static							
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$		-	-	V	
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \mu A$	2.5	-	4	V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$	-	-	± 100	nA	
		V _{DS} = 250 V, V _{GS} = 0 V	-	-	1		
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 250 V, V _{GS} = 0 V, T _J = 125 °C	-	-	50	μА	
		$V_{DS} = 250 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 175 ^{\circ}\text{C}$	-	-	250		
On-State Drain Current ^b	I _{D(on)}	$V_{DS} = 15 \text{ V}, V_{GS} = 10 \text{ V}$	17	-	-	Α	
		V _{GS} = 10 V, I _D = 14 A	-	0.131	31 0.165		
Drain-Source On-State Resistance b	R _{DS(on)}	$V_{GS} = 10 \text{ V}, I_D = 14 \text{ A}, T_J = 125 ^{\circ}\text{C}$	-	-	0.347		
		$V_{GS} = 10 \text{ V}, I_D = 14 \text{ A}, T_J = 175 ^{\circ}\text{C}$	-	-	0.462		
Forward Transconductance b	9 _{fs}	$V_{DS} = 15 \text{ V}, I_{D} = 17 \text{ A}$	-	36	-	S	
Dynamic ^a							
Input Capacitance	C _{iss}		-	1950	-	pF	
Output Capacitance	C _{oss}	$V_{GS} = 0 \text{ V}, V_{DS} = 25 \text{ V}, f = 1 \text{ MHz}$	-	160	-		
Reverse Transfer Capacitance	C _{rss}		-	70	-		
Total Gate Charge ^c	Qg		-	30	42		
Gate-Source Charge ^c	Q_{gs}	$V_{DS} = 125 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 17 \text{ A}$	-	10	-	nC	
Gate-Drain Charge ^c	Q_{gd}		-	10	-		
Gate Resistance	R_g		-	1.6	-	Ω	
Turn-On Delay Time ^c	t _{d(on)}		-	15	25		
Rise Time ^c	t _r	$V_{DD} = 125 \text{ V}, R_1 = 7.35 \Omega$	-	130	195	ns	
Turn-Off Delay Time ^c	t _{d(off)}	$I_D \cong 17 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 2.5 \Omega$	-	30	45		
Fall Time ^c	t _f		-	100	150		
Source-Drain Diode Ratings and Cha	racteristics (T _C = 25 °C)					
Pulsed Current	I _{SM}		-	-	20	Α	
Diode Forward Voltage b	V_{SD}	I _F = 17 A, V _{GS} = 0 V	-	0.9	1.5	V	
Source-Drain Reverse Recovery Time	t _{rr}	I _F = 17 A, dl/dt = 100 A/μs	_	115	175	ns	

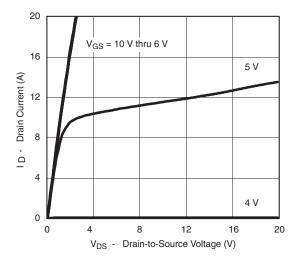
Notes

- a. Guaranteed by design, not subject to production testing.
- b. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%$
- c. Independent of operating temperature.

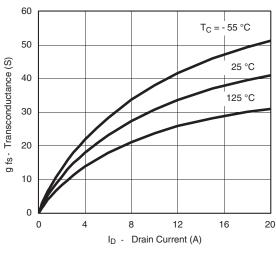
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



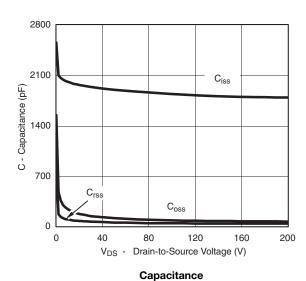
TYPICAL CHARACTERISTICS (25 °C unless otherwise noted)



Output Characteristics

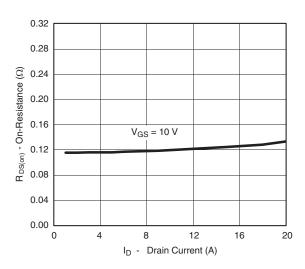


Transconductance

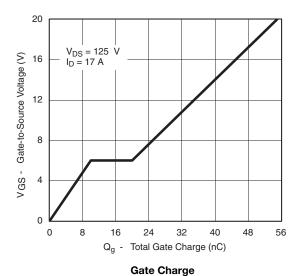


20 16 I_D - Drain Current (A) 12 8 T_C = 125 °C 4 25 °C - 55 °C 0 0 2 3 5 6 V_{GS} - Gate-to-Source Voltage (V)

Transfer Characteristics

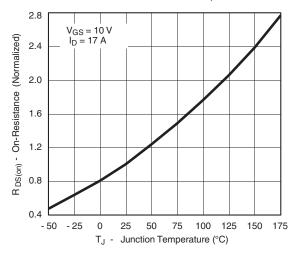


On-Resistance vs. Drain Current

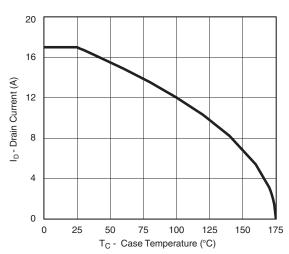




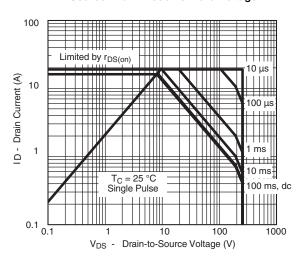
TYPICAL CHARACTERISTICS (25 °C unless otherwise noted)



On-Resistance vs. Junction Temperature

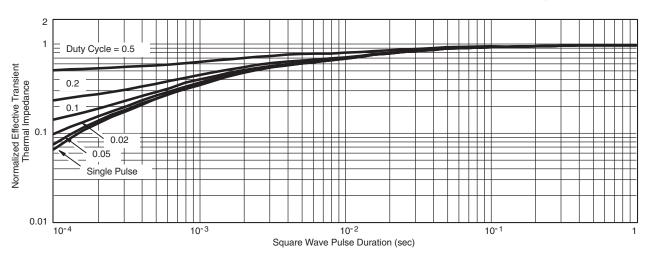


Source-Drain Diode Forward Voltage



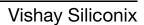
Max. Avalanche Drain Current vs. Case Temperature





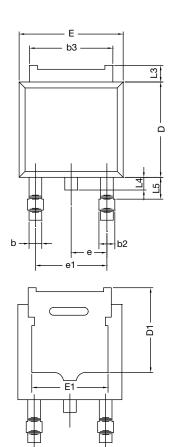
Normalized Thermal Transient Impedance, Junction-to-Case

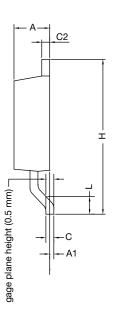
Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?72851.





TO-252AA Case Outline



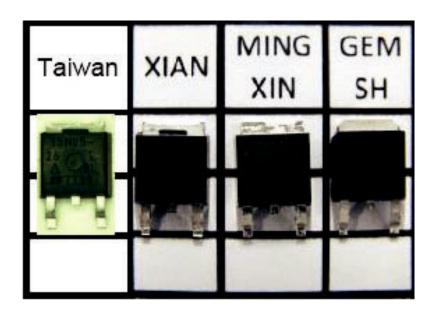


	MILLIMETERS		INCHES		
DIM.	MIN.	MAX.	MIN.	MAX.	
Α	2.18	2.38	0.086	0.094	
A1	-	0.127	-	0.005	
b	0.64	0.88	0.025	0.035	
b2	0.76	1.14	0.030	0.045	
b3	4.95	5.46	0.195	0.215	
С	0.46	0.61	0.018	0.024	
C2	0.46	0.89	0.018	0.035	
D	5.97	6.22	0.235	0.245	
D1	4.10	-	0.161	-	
Е	6.35	6.73	0.250	0.265	
E1	4.32	-	0.170	-	
Н	9.40	10.41	0.370	0.410	
е	2.28	BSC	0.090 BSC		
e1	4.56	BSC	0.180	BSC	
L	1.40	1.78	0.055	0.070	
L3	0.89	1.27	0.035	0.050	
L4	=	1.02	-	0.040	
L5	1.01	1.52	0.040	0.060	
ECN: T13-0359-Rev. O, 03-Jun-13					

DWG: 5347

Notes

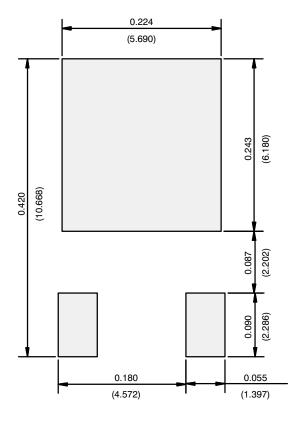
- Dimension L3 is for reference only.
- Xi'an, Mingxin, and GEM SH actual photo.



Revision: 03-Jun-13 Document Number: 71197



RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads Dimensions in Inches/(mm)

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APPLICATION NOTE



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Revision: 02-Oct-12 Document Number: 91000

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SUD17N25-165-E3